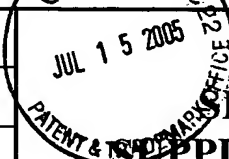


First Named Inventor	Leonard Forbes	 <p><b>SECOND SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT</b></p>
Serial No.	10/785,310	
Filing Date	February 24, 2004	
Group Art Unit	2818	
Examiner Name	Tu Tu V. Ho	
Allowed	April 28, 2005	
Confirmation No.	9673	
Attorney Docket No.	400.264US01	
Title: 4F2 EEPROM NROM MEMORY ARRAYS WITH VERTICAL DEVICES		

Mail Stop: RCE  
 Commissioner for Patents  
 P.O. Box 1450  
 Alexandria, VA 22313-1450

In compliance with 37 C.F.R. §§ 1.56 and 1.97, *et seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified Application.

Pursuant to 37 C.F.R. 1.98 (a)(2)(i), as this application was filed after June 30, 2003, Applicant has not included copies of U.S. Patents or U.S. Patent Applications. Applicant respectfully requests that this Supplemental Information Disclosure Statement be entered and the references listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to MPEP §609, Applicant further requests that the Examiner initial next to each reference on the Form 1449 to indicate that the listed references have been considered. Applicant further requests that a copy of the initialed Form 1449 be returned with the next official communication.


A copy of the International Search Report is enclosed herewith.

As this Second Supplemental Information Disclosure Statement is being filed together with a Request for Continuing Examination (RCE), Applicant believes that no fees are due. However, the Commissioner for Patents is hereby authorized to charge any additional fees to Deposit Account No. 501373.


If the Examiner has any questions or concerns regarding this application, please contact the undersigned at (612) 312-2207.

Respectfully submitted,

Date: 7/15/05

  
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Examiner Signature		Date Considered	
*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.			

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